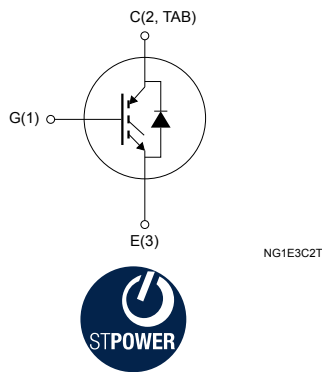
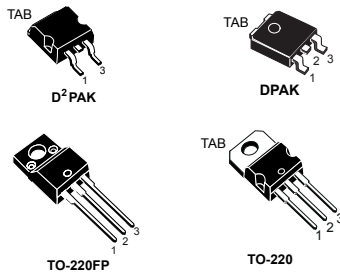




STGB10NC60KDT4, STGD10NC60KDT4 STGF10NC60KD, STGP10NC60KD

Datasheet

10 A, 600 V short-circuit rugged IGBT



Features

- Lower on voltage drop ($V_{CE(sat)}$)
- Lower C_{res} / C_{ies} ratio (no cross-conduction susceptibility)
- Very soft ultra-fast recovery antiparallel diode
- Short-circuit withstand time 10 μs

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

Description

These devices are very fast IGBTs developed using advanced PowerMESH technology. This process guarantees an excellent trade-off between switching performance and low on-state behavior. These devices are well-suited for resonant or soft-switching applications.

Product status links

[STGB10NC60KDT4](#)

[STGD10NC60KDT4](#)

[STGF10NC60KD](#)

[STGP10NC60KD](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		D ² PAK, TO-220	DPAK	TO-220FP	
V _{CES}	Collector-emitter voltage (V _{GE} = 0 V)	600			V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	20		9	A
	Continuous collector current at T _C = 100 °C	10		6	
I _{CL} ⁽²⁾	Turn-off latching current	30			A
I _{CP} ⁽³⁾	Pulsed collector current	30			A
V _{GE}	Gate-emitter voltage	±20			V
I _F	Diode RMS forward current at T _C = 25 °C	10			A
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal	20			A
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T _C = 25 °C)			2.5	kV
t _{scw}	Short-circuit withstand time V _{CE} = 0.5, V _{CES} , T _J = 125 °C, R _G = 10 Ω, V _{GE} = 12 V	10			μs
P _{TOT}	Total power dissipation at T _C = 25 °C	65	62	25	W
T _{stg}	Storage temperature range	-55 to 150			°C
T _J	Operating junction temperature range				°C

1. Calculated according to the iterative formula:
$$I_C(T_C) = \frac{T_{J(max)} - T_C}{R_{thJC} \times V_{CE(sat)(max)}(T_{J(max)}, I_C(T_C))}$$
2. V_{clamp} = 80% V_{CES}, T_J = 150 °C, R_G = 10 Ω, V_{GE} = 15 V.
3. Pulse width limited by maximum junction temperature and turn-off within RBSOA.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		D ² PAK, TO-220	DPAK	TO-220FP	
R _{thJC}	Thermal resistance, junction-to-case IGBT	1.9	2	5	°C/W
	Thermal resistance, junction-to-case diode	4	4.5	7	
R _{thJA}	Thermal resistance, junction-to-ambient	62.5	100	62.5	°C/W

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$, $I_C = 1\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$		2.2	2.5	V
		$V_{GE} = 15\text{ V}$, $I_C = 5\text{ A}$, $T_J = 150\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	4.5		6.5	V
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$			0.15	mA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 125\text{ °C}$ ⁽¹⁾			1	
I_{GES}	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			± 100	nA
g_{fs} ⁽²⁾	Forward transconductance	$V_{CE} = 15\text{ V}$, $I_C = 5\text{ A}$		15		S

1. Specified by design, not tested in production.

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0\text{ V}$	-	380	-	pF
C_{oes}	Output capacitance		-	46	-	pF
C_{res}	Reverse transfer capacitance		-	8.5	-	pF
Q_g	Total gate charge	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $V_{GE} = 0\text{ to }15\text{ V}$ (see Figure 19. Gate charge test circuit)	-	19	-	nC
Q_{ge}	Gate-emitter charge		-	5	-	nC
Q_{gc}	Gate-collector charge		-	9	-	nC

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	17	-	ns
t_r	Current rise time		-	6	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	655	-	A/ μ s
$t_{d(on)}$	Turn-on delay time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	16.5	-	ns
t_r	Current rise time		-	6.5	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	575	-	A/ μ s
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	33	-	ns
$t_{d(off)}$	Turn-off delay time		-	72	-	ns
t_f	Current fall time		-	82	-	ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching and Figure 20. Switching waveform)	-	60	-	ns
$t_{d(off)}$	Turn-off delay time		-	106	-	ns
t_f	Current fall time		-	136	-	ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$ (see Figure 17. Test circuit for inductive load switching)	-	55	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	85	-	μ J
E_{ts}	Total switching energy		-	140	-	μ J
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 17. Test circuit for inductive load switching)	-	87	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	162	-	μ J
E_{ts}	Total switching energy		-	249	-	μ J

1. Including the reverse recovery of the diode.

2. Including the tail of the collector current.

Table 7. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_F	Forward on-voltage	$I_F = 5\text{ A}$	-	2	-	V
		$I_F = 5\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$	-	1.6	-	
t_{rr}	Reverse recovery time	$I_F = 5\text{ A}$, $V_R = 40\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$ (see Figure 18. Diode reverse recovery waveform)	-	22	-	ns
Q_{rr}	Reverse recovery charge		-	14	-	nC
I_{rrm}	Reverse recovery current		-	1.3	-	A
t_{rr}	Reverse recovery time	$I_F = 5\text{ A}$, $V_R = 40\text{ V}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 18. Diode reverse recovery waveform)	-	35	-	ns
Q_{rr}	Reverse recovery charge		-	40	-	nC
I_{rr}	Reverse recovery current		-	2.2	-	A

2.1 Electrical characteristics (curves)

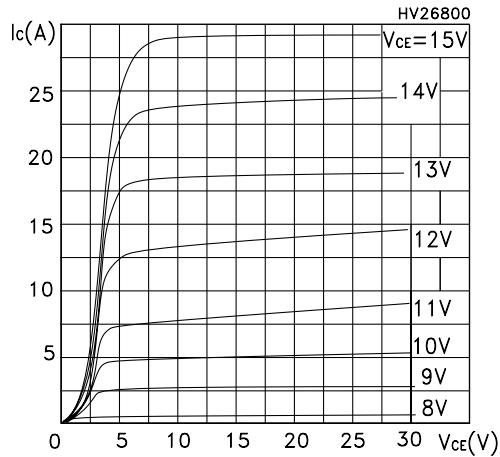
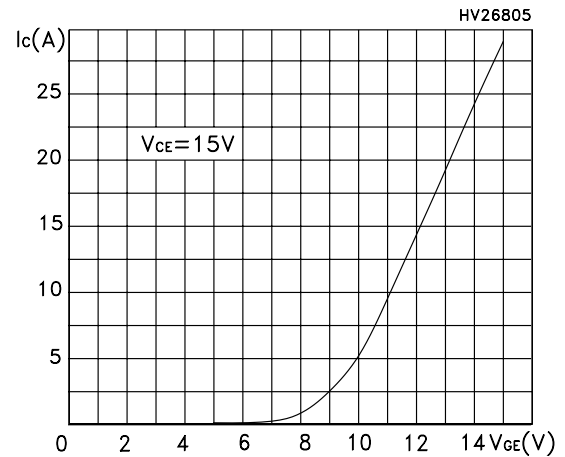
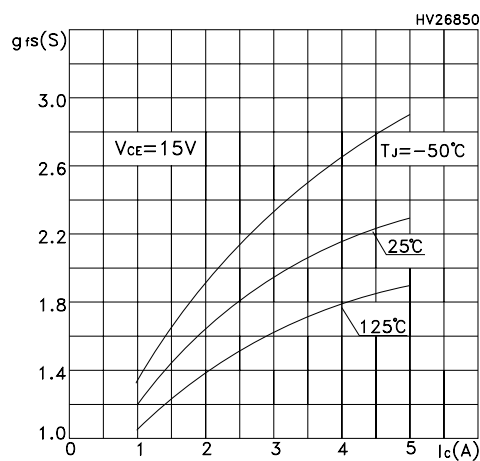
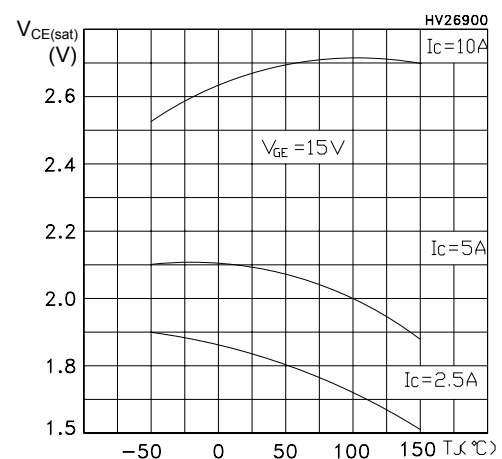
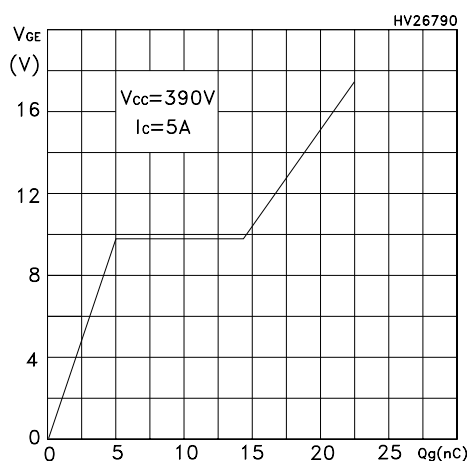
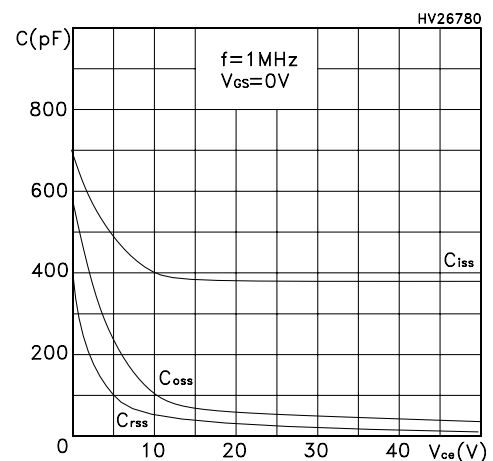
Figure 1. Typical output characteristics

Figure 2. Typical transfer characteristics

Figure 3. Typical transconductance characteristics

Figure 4. Typical collector-emitter on voltage vs temperature

Figure 5. Typical gate charge characteristics

Figure 6. Typical capacitance characteristics


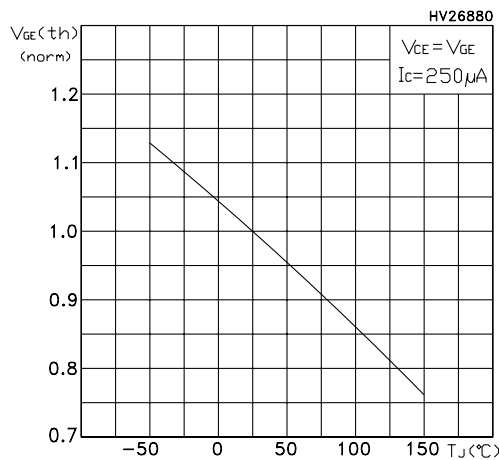
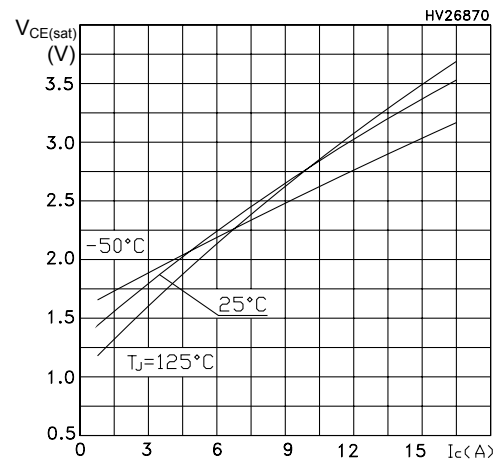
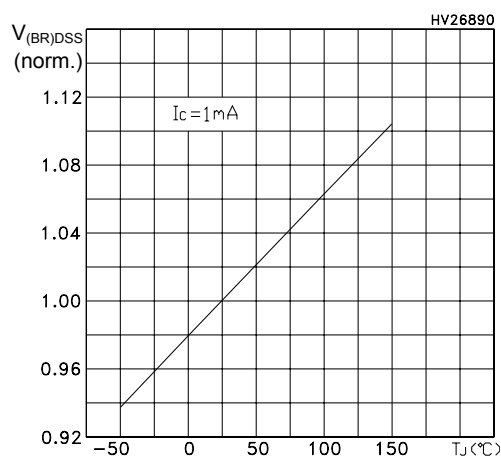
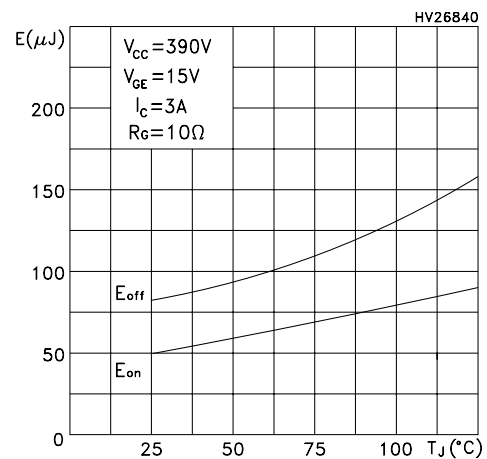
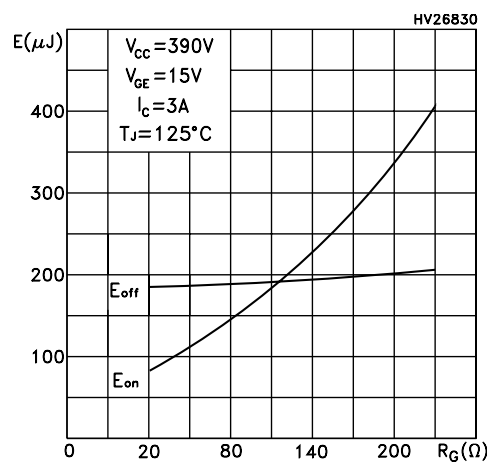
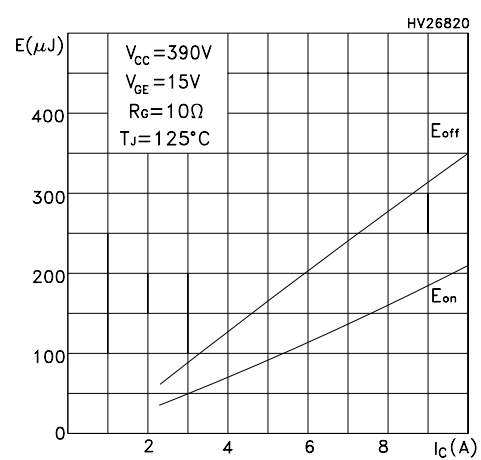
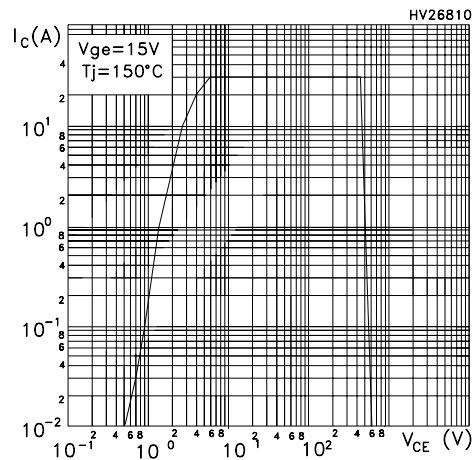
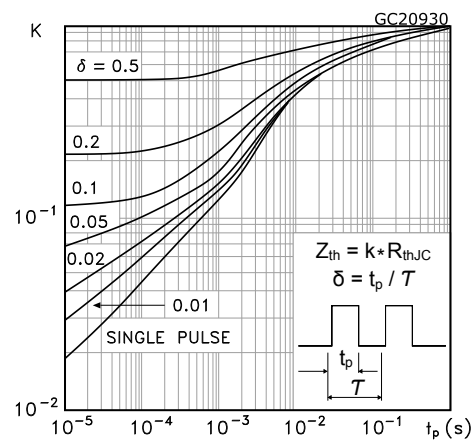
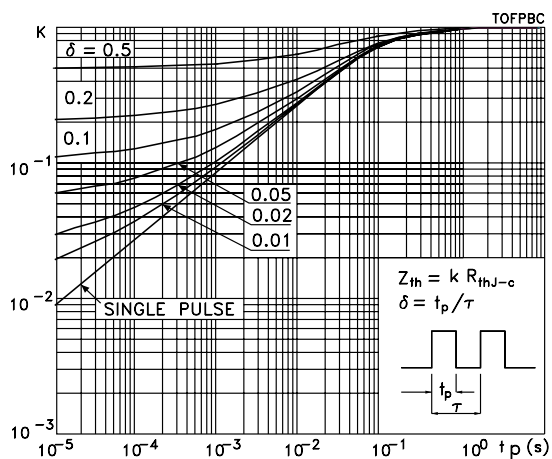
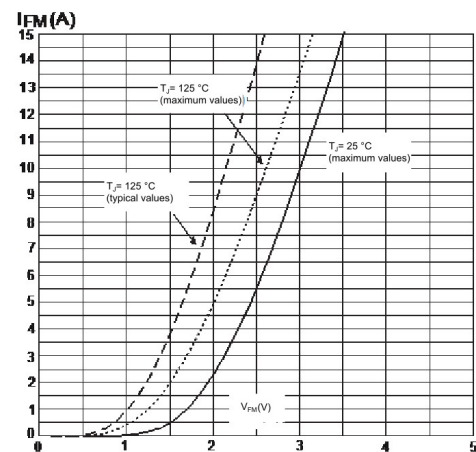
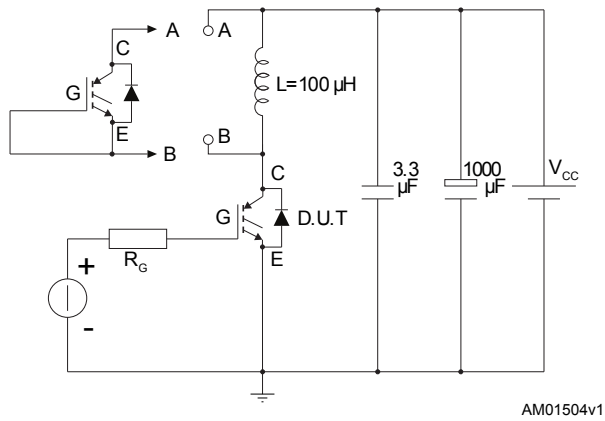
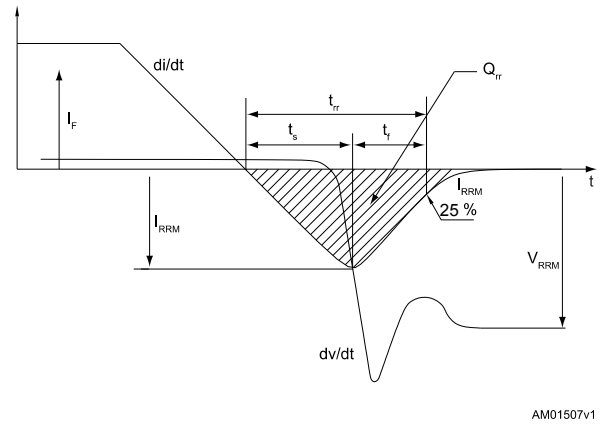
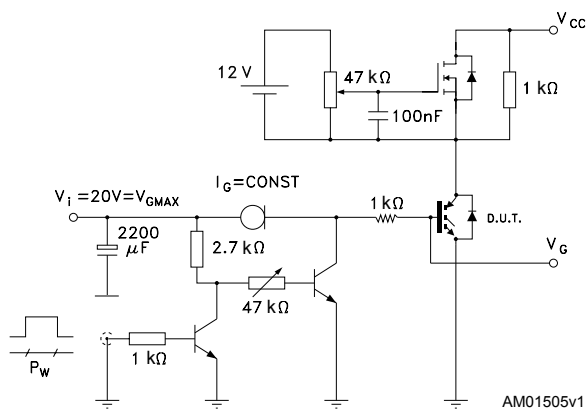
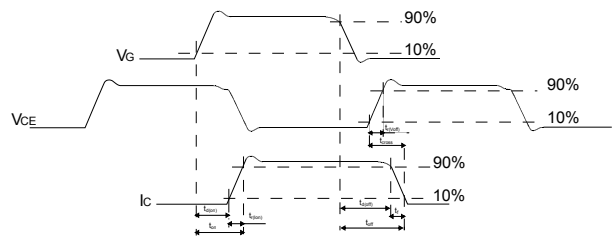
Figure 7. Normalized gate threshold vs temperature

Figure 8. Typical collector-emitter on voltage vs collector current

Figure 9. Normalized breakdown voltage vs temperature

Figure 10. Typical switching energy vs temperature

Figure 11. Typical switching energy vs gate resistance

Figure 12. Typical switching energy vs collector current


Figure 13. Reverse bias safe operating area

Figure 14. Normalized transient thermal impedance for D²PAK, DPAK and TO-220

Figure 15. Normalized transient thermal impedance for TO-220FP

Figure 16. Typical emitter-collector diode characteristics


3 Test circuits

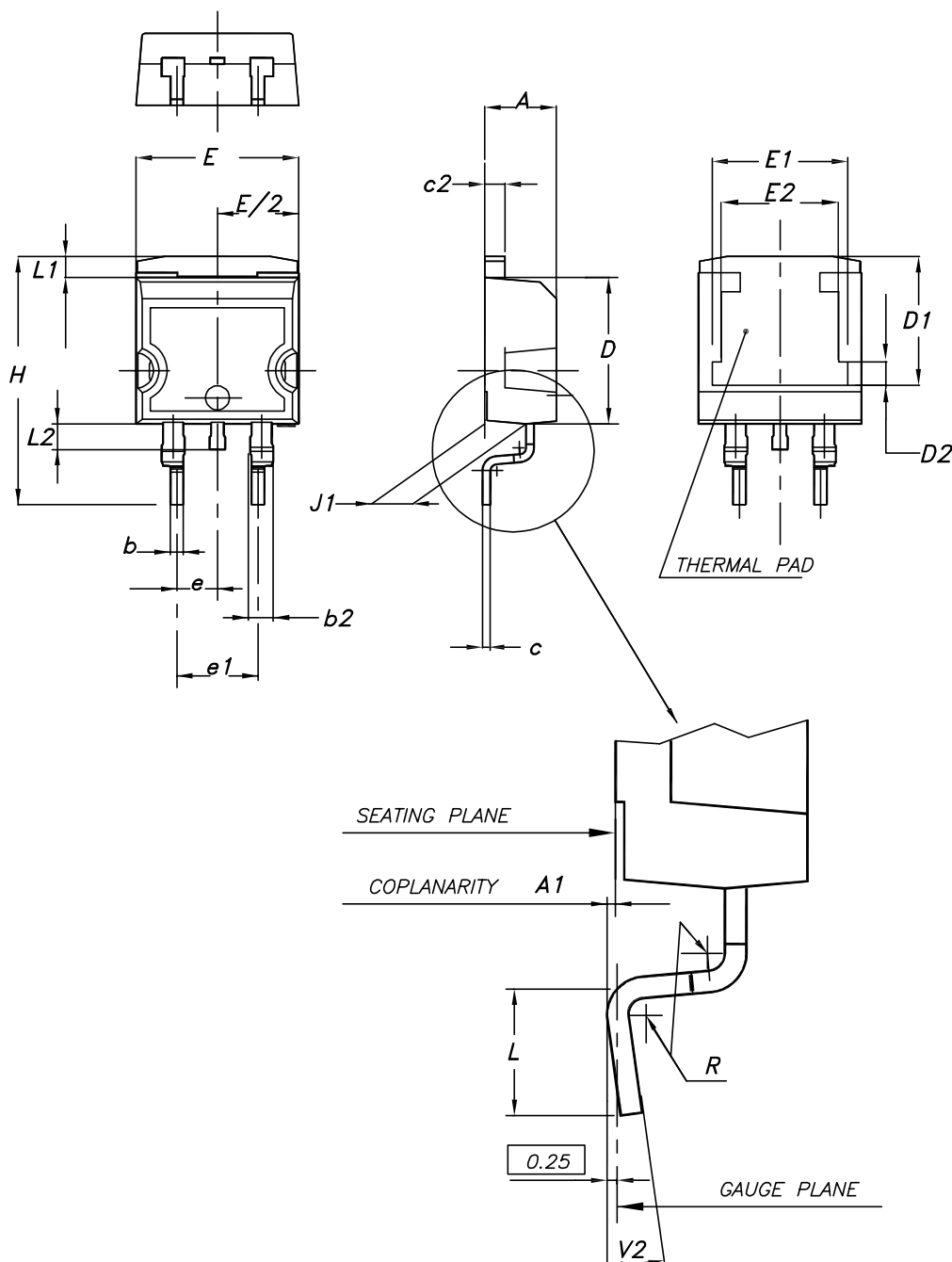
Figure 17. Test circuit for inductive load switching

Figure 18. Diode reverse recovery waveform

Figure 19. Gate charge test circuit

Figure 20. Switching waveform


4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

Figure 21. D²PAK (TO-263) type A package outline



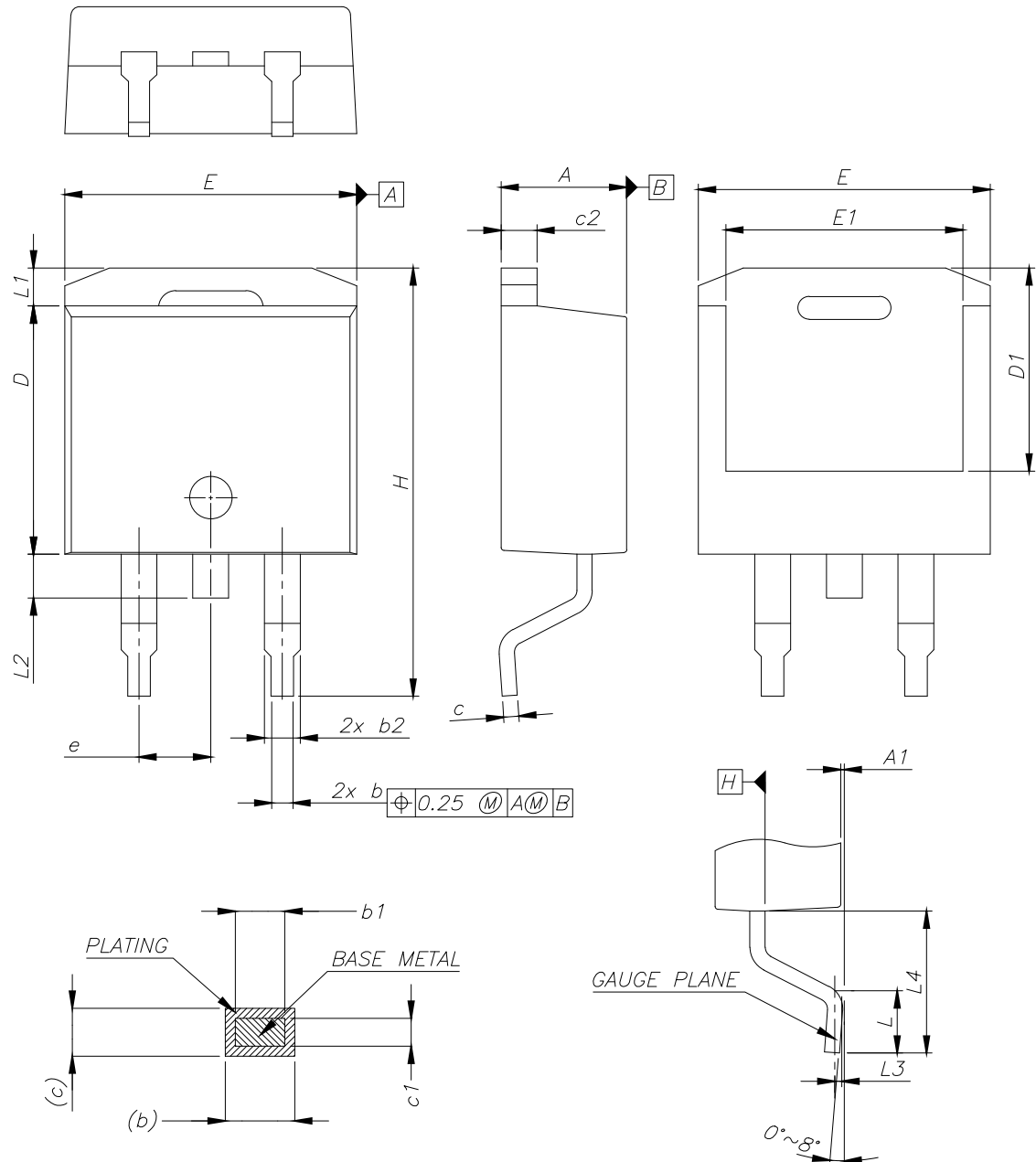
0079457_27

Table 8. D²PAK (TO-263) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

4.2 D²PAK (TO-263) type B package information

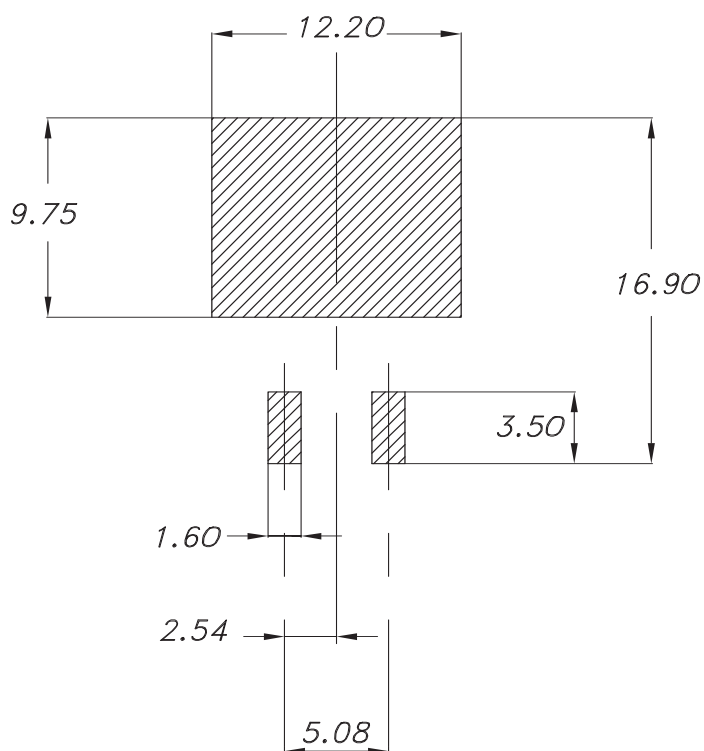
Figure 22. D²PAK (TO-263) type B package outline



0079457_27_B

Table 9. D²PAK (TO-263) type B mechanical data

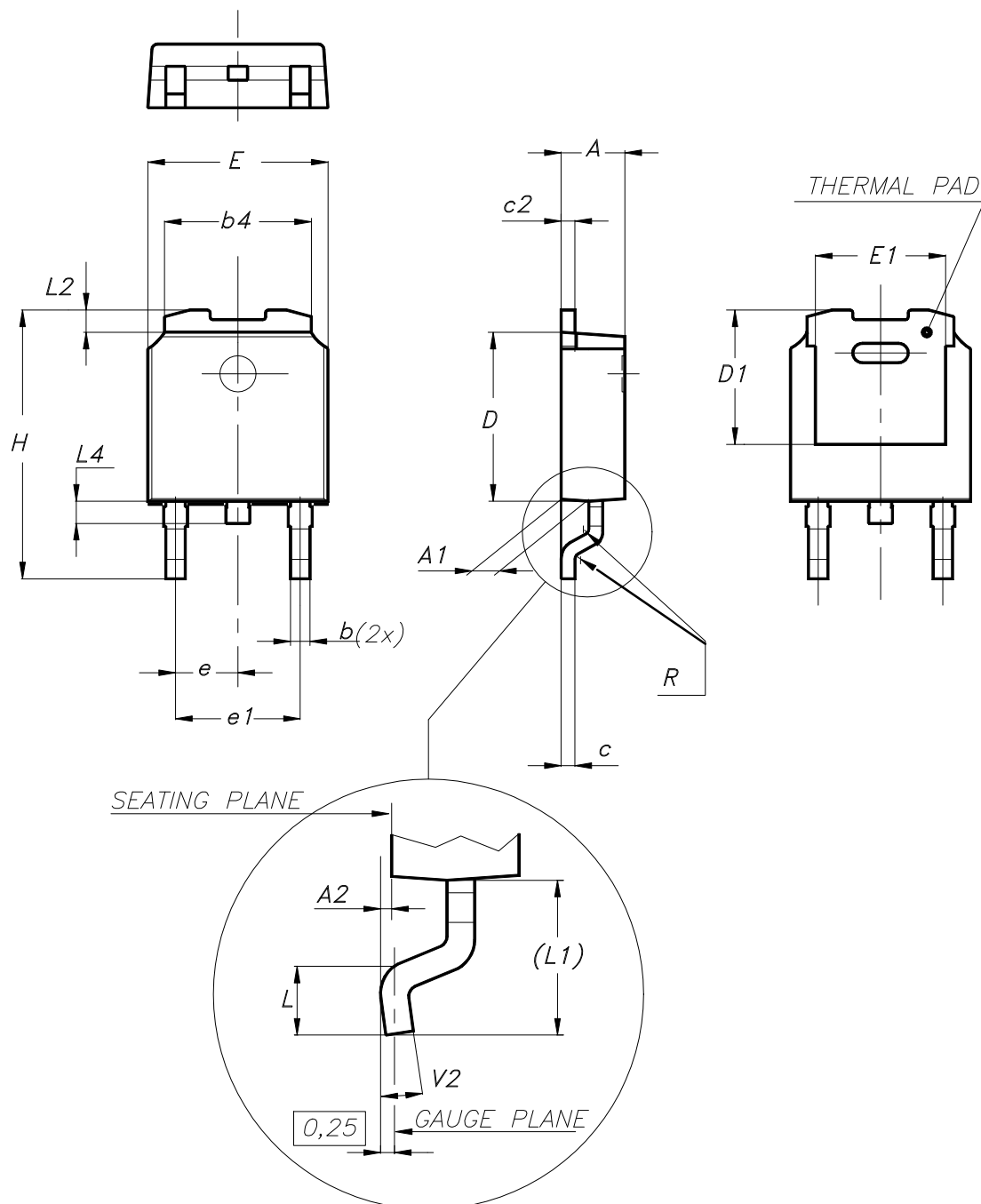
Dim.	mm		
	Min.	Typ.	Max.
A	4.36		4.56
A1	0.00		0.25
b	0.70		0.90
b1	0.51		0.89
b2	1.17		1.37
c	0.38		0.694
c1	0.38		0.534
c2	1.19		1.34
D	8.60		9.00
D1	6.90		7.50
E	10.15		10.55
E1	8.10		8.70
e	2.54 BSC		
H	15.00		15.60
L	1.90		2.50
L1			1.65
L2			1.78
L3		0.25	
L4	4.78		5.28

Figure 23. D²PAK (TO-263) recommended footprint (dimensions are in mm)


0079457_Rev27_footprint

4.3 DPAK (TO-252) type A package information

Figure 24. DPAK (TO-252) type A package outline



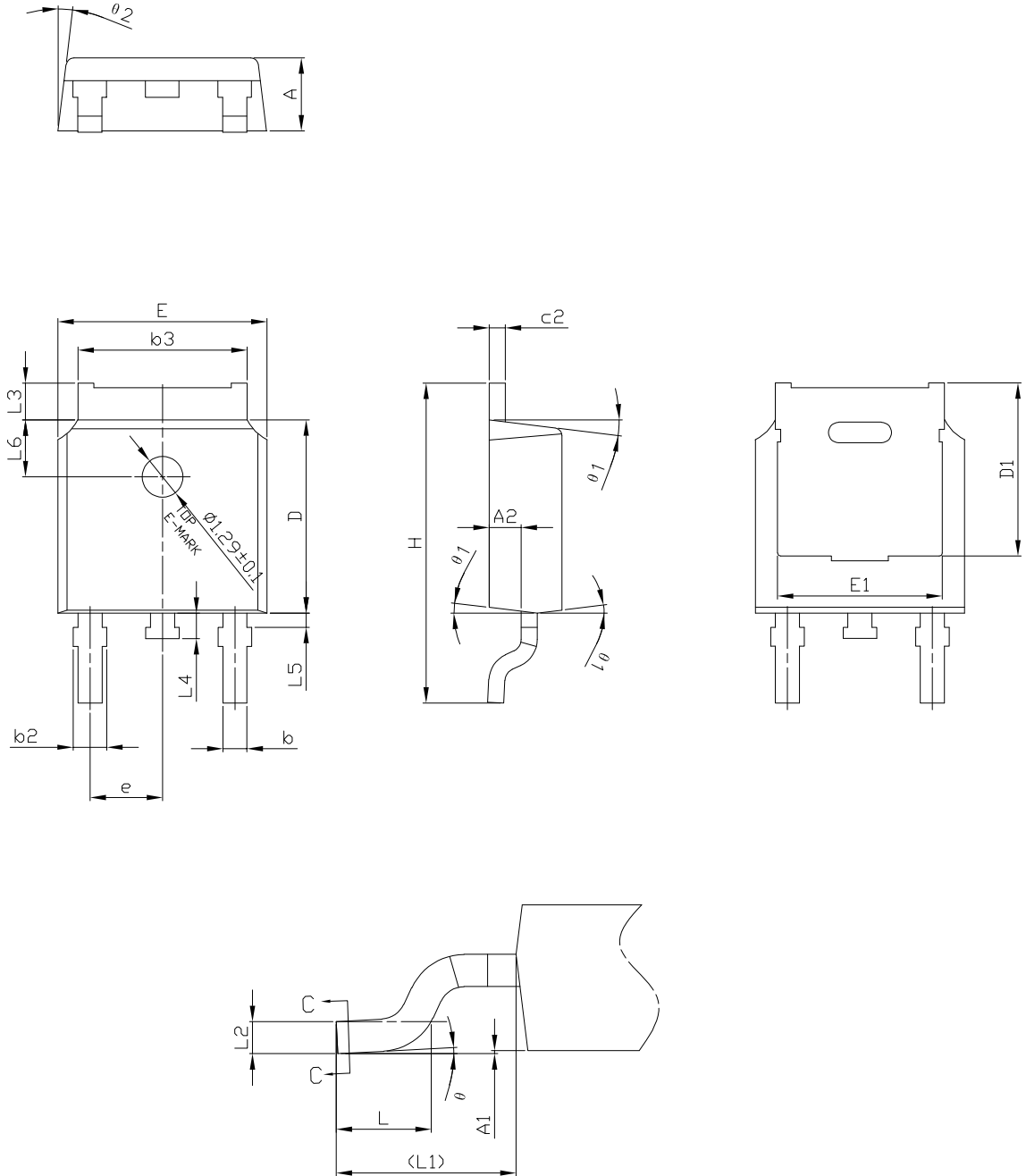
0068772_A_35

Table 10. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.4 DPAK (TO-252) type C3 package information

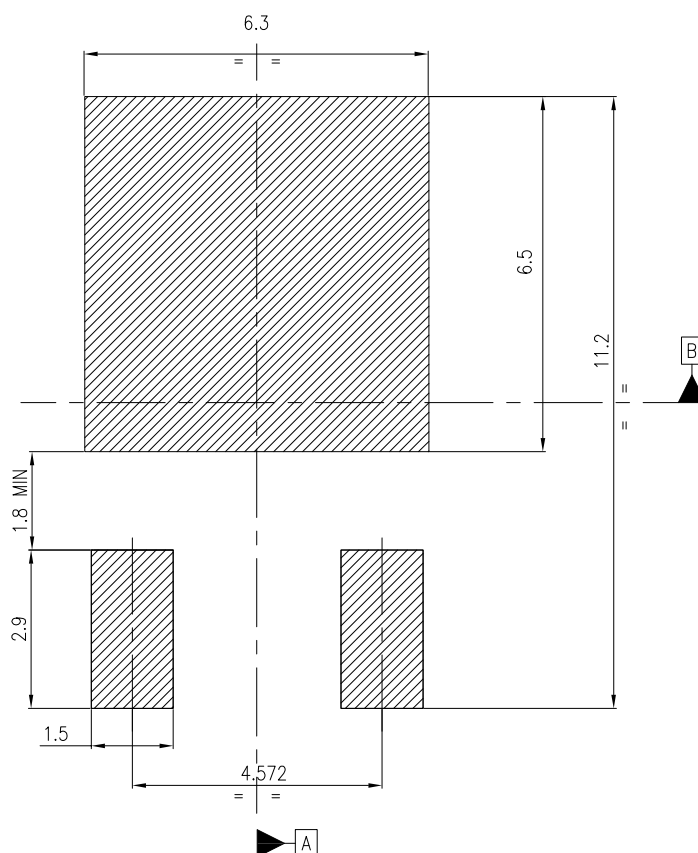
Figure 25. DPAK (TO-252) type C3 package outline



0068772_type-C3_rev35

Table 11. DPAK (TO-252) type C3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.00		0.10
A2	0.90	1.01	1.10
b	0.72		0.85
b2	0.72		1.10
b3	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.20	5.45	5.70
E	6.50	6.60	6.70
E1	5.00	5.20	5.40
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.51 BSC		
L3	0.90		1.25
L4	0.60	0.80	1.00
L5	0.15		0.75
L6	1.80 REF		
θ	0°		8°
θ1	5°	7°	9°
θ2	5°	7°	9°

Figure 26. DPAK (TO-252) recommended footprint (dimensions are in mm)


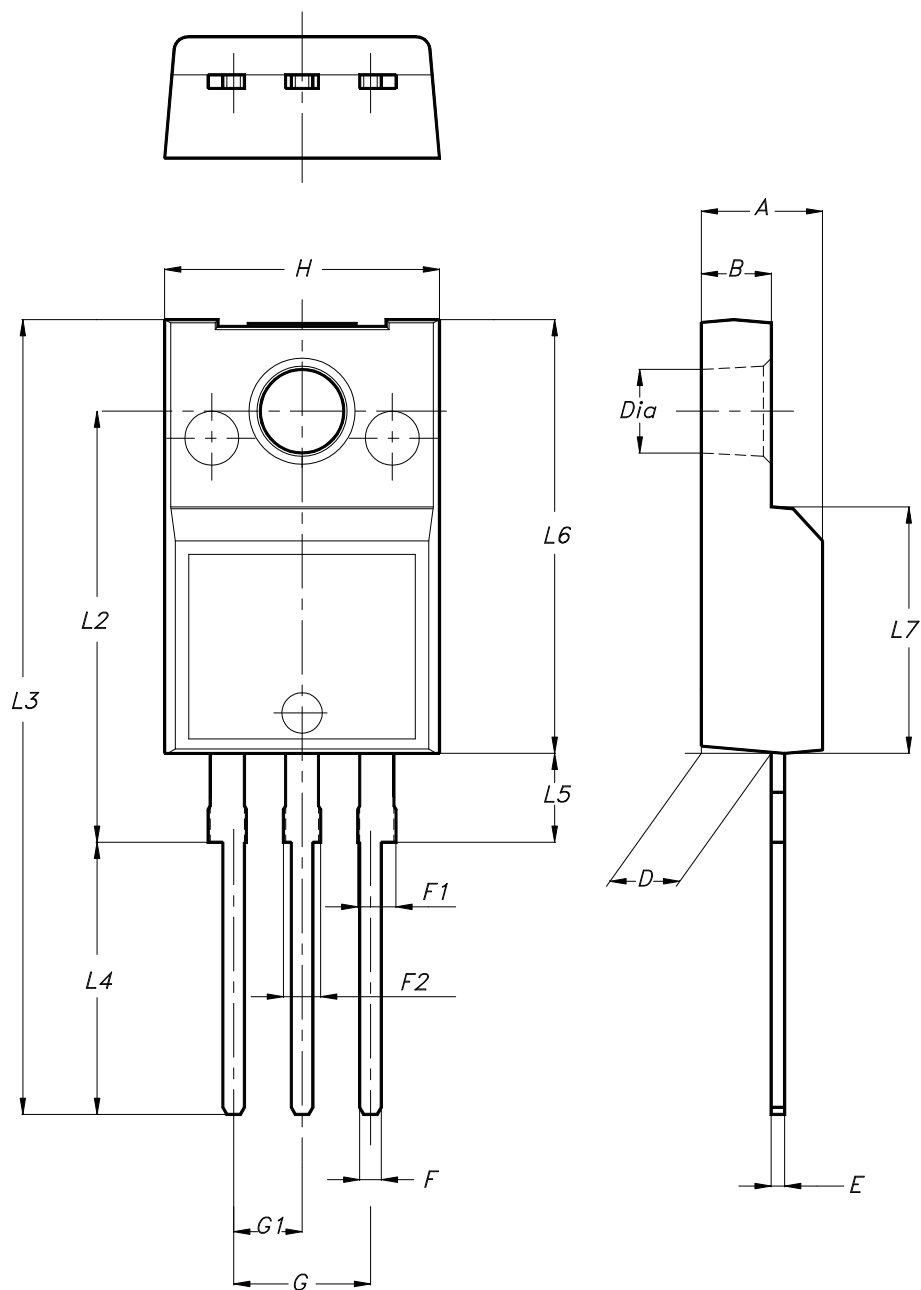
Notes:

- 1) This footprint is able to ensure insulation up to 630 Vrms (according to CEI IEC 664-1)
- 2) The device must be positioned within $\boxed{\Phi 0.05 \text{ A B}}$

FP_0068772_35

4.5 TO-220FP type B package information

Figure 27. TO-220FP type B package outline



7012510_B_rev.14

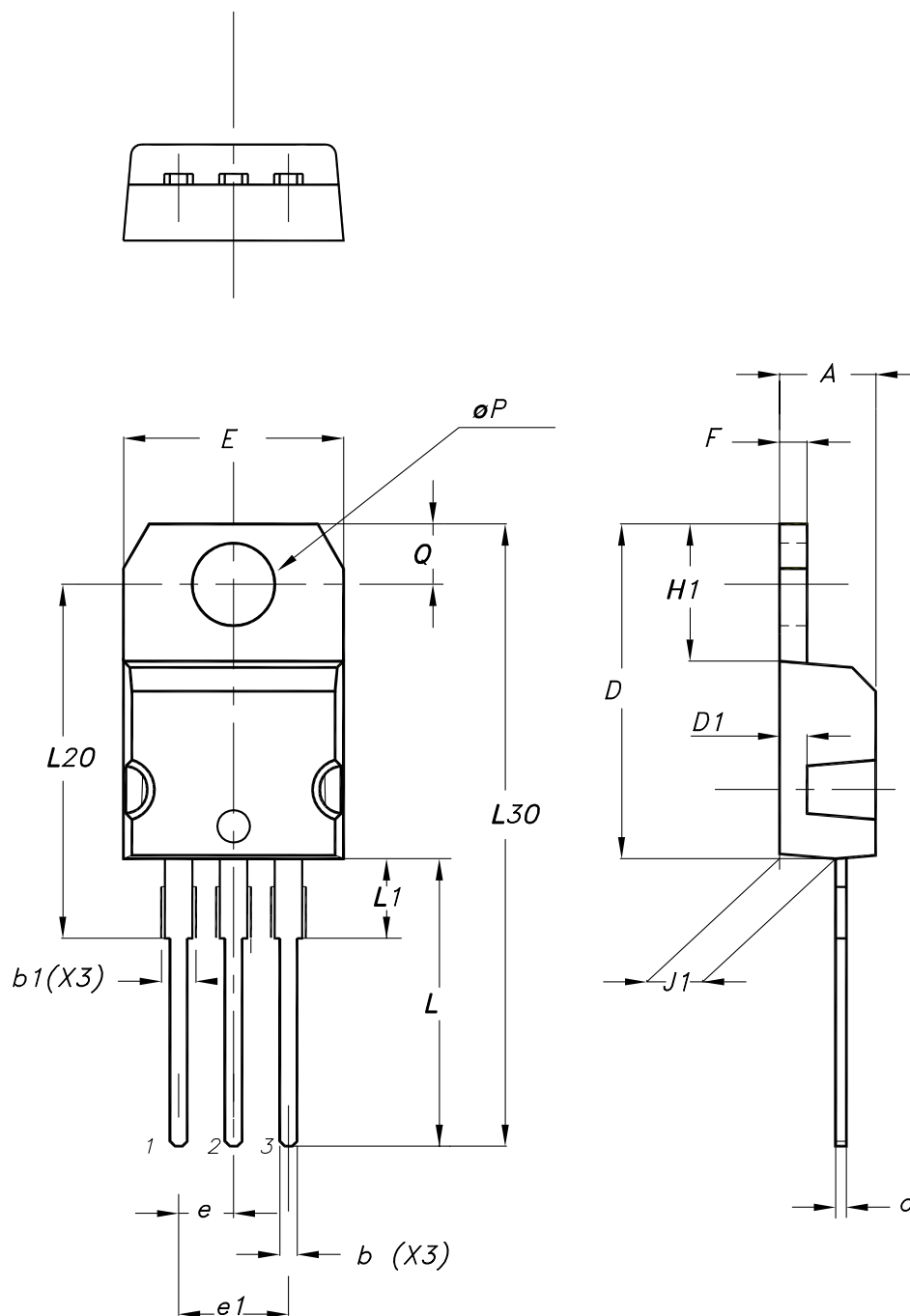


Table 12. TO-220FP type B package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.70
F	0.75		1.00
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.20
G1	2.40		2.70
H	10.00		10.40
L2		16.00	
L3	28.60		30.60
L4	9.80		10.60
L5	2.90		3.60
L6	15.90		16.40
L7	9.00		9.30
Dia	3.00		3.20

4.6 TO-220 type A package information

Figure 28. TO-220 type A package outline



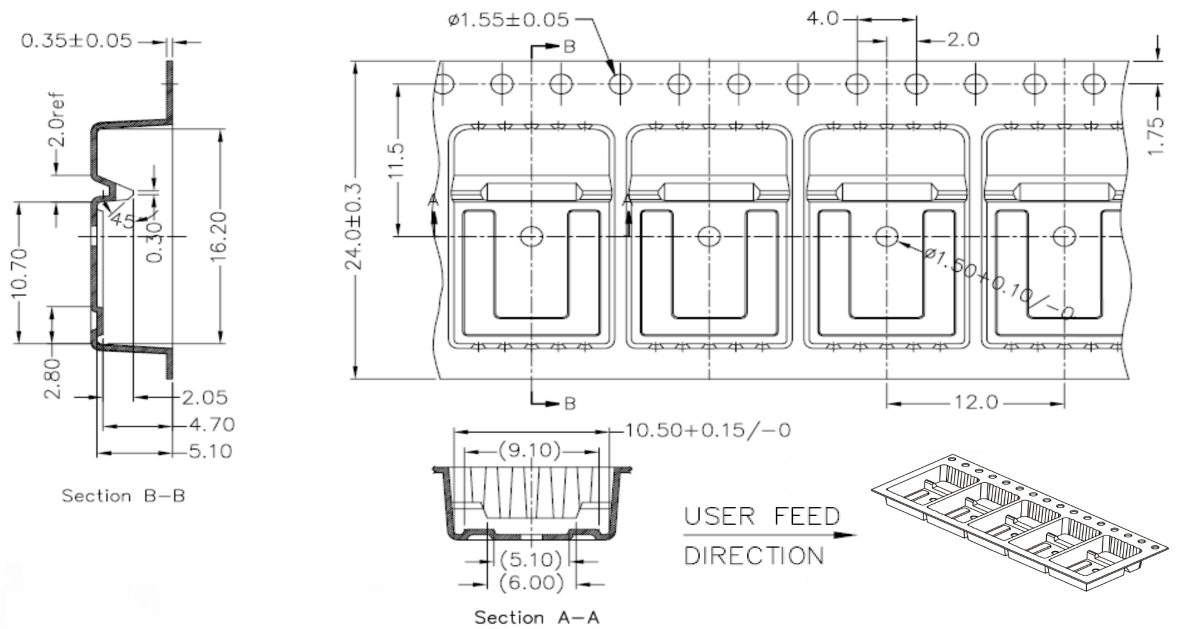
0015988_typeA_Rev_24

Table 13. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

4.7 D²PAK packing information

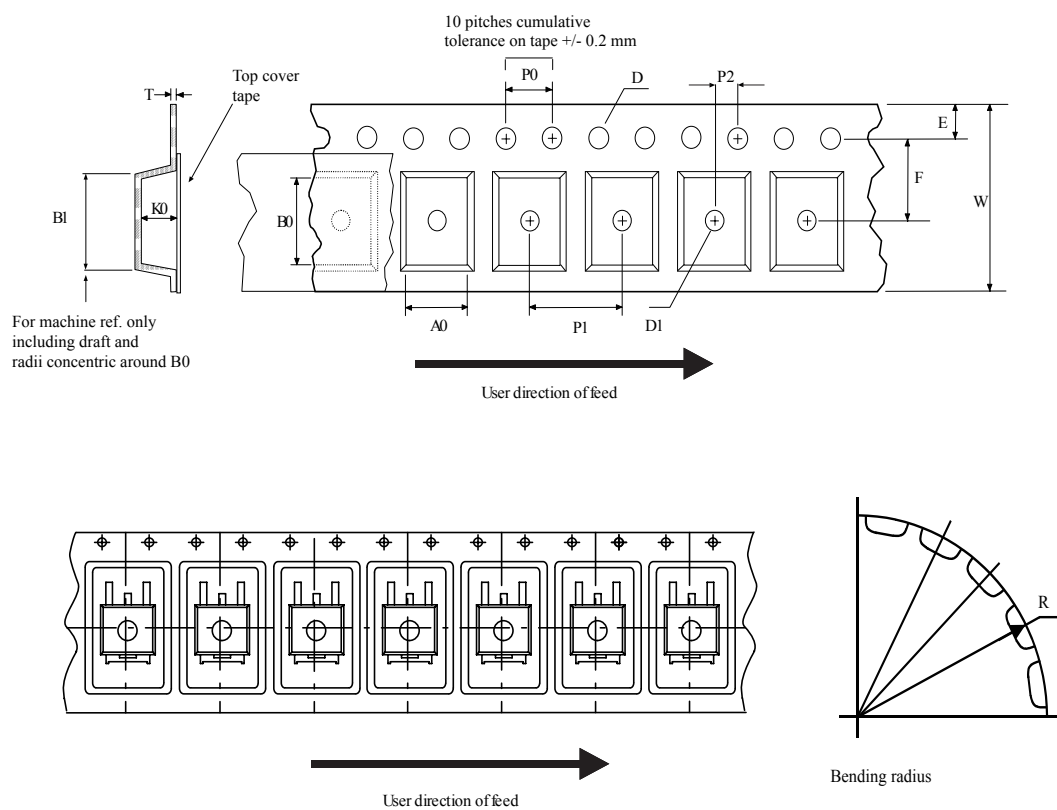
Figure 29. D²PAK tape drawing (dimensions are in mm)



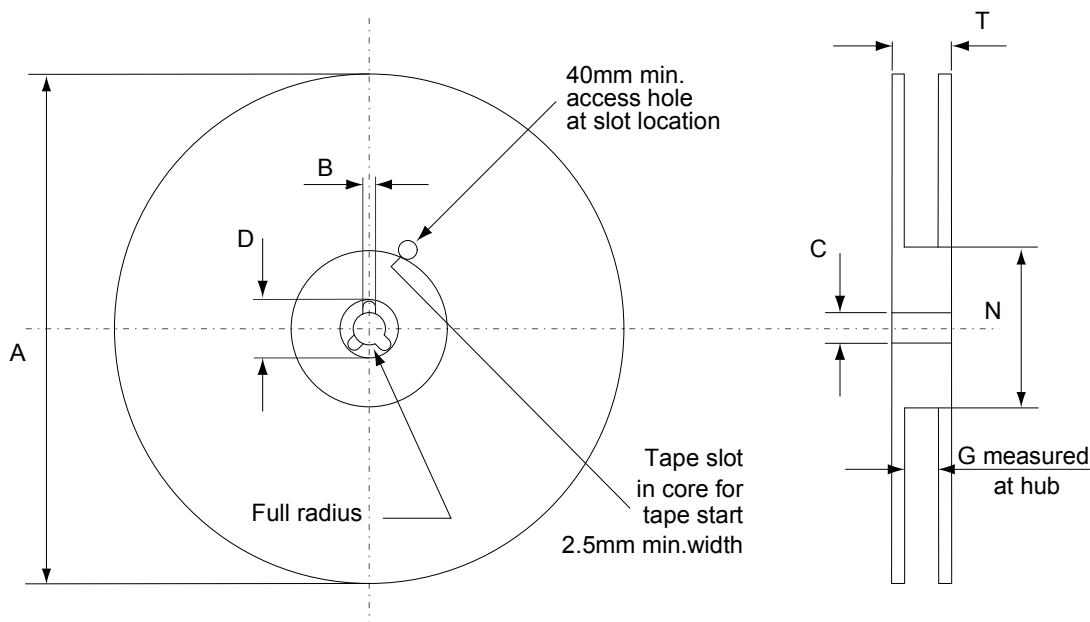
DM01095771_1

4.8 DPAK (TO-252) packing information

Figure 30. DPAK (TO-252) tape outline



AM08852v1

Figure 31. DPAK (TO-252) reel outline


AM06038v1

Table 14. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			



5 Ordering information

Table 15. Order codes

Order codes	Marking	Package	Packing
STGB10NC60KDT4	GB10NC60KD	D ² PAK	Tape and reel
STGD10NC60KDT4	GD10NC60KD	DPAK	
STGF10NC60KD	GF10NC60KD	TO-220FP	Tube
STGP10NC60KD	GP10NC60KD	TO-220	



Revision history

Table 16. Document revision history

Date	Revision	Changes
14-Jun-2005	1	First release.
19-Jul-2005	2	Complete version.
27-Jan-2006	3	Inserted ecopack indication.
01-Mar-2006	4	The document has been reformatted.
08-Feb-2007	5	Modified value on <i>Table 6.: Switching on/off (inductive load)</i> .
24-Nov-2009	6	Inserted DPAK package option.
06-Jun-2017	7	Modified part numbers on cover page. Updated <i>Section 4: "Package information"</i> . Minor text changes.
26-May-2023	8	Updated the entire Section 4: Package information. Minor text changes.
09-May-2025	9	Updated Section 4: Package information .



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